

State Key Laboratory of Silicon Materials, Department of Materials Science and Engineering, Zhejiang University, Hangzhou, P. R. of China

Amorphous oxide semiconductors (AOSs) are emerging as promising materials for the active layers of thin film transistors (TFTs), which are used in active-matrix liquid crystal display (AMLCD) and active

## Experimental

## The channel layer deposition:

- > Via PLD (10Hz; 300 mJ)
- Ceramic target
- Room temperature
- > Oxygen partial pressure: 6.7 Pa
- ➤ Substrate-target distance: 4.5 ~ 6 cm
- Thickness: 50 nm
- ➤ Annealing at 400 °C in air

Fig. 2. Schematic of an *a*-InGaZnO TFT in a bottom-gate coplanar configuration.

## Results and discussion

## B. Stability of annealed a-InGaZnO TFTs The stability of annealed a-InGaZnO TFTs The stability of annealed a-InGaZnO TFTs The stability of annealed a-InGaZnO TFTs Stress time (s) The stability of annealed a-InGaZnO TFTs Stress time (s)

Conclusions